

Abstract of the Disclosure

An MOS device is formed including a semiconductor layer of a first conductivity type, a first source/drain region of a second conductivity type formed in the semiconductor layer, and a second source/drain region of the second conductivity type formed in the semiconductor layer and spaced
5 apart from the first source/drain region. A gate is formed proximate an upper surface of the semiconductor layer and at least partially between the first and second source/drain regions. The MOS device further includes at least one contact, the at least one contact including a silicide layer formed on and in electrical connection with at least a portion of the first source/drain region, the silicide layer extending laterally away from the gate. The contact further includes at least one
10 insulating layer formed directly on the silicide layer.